

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S182	32	((((438/778) or (438/791) or (438/758) or (438/763) or (438/792) or (438/786)).CCLS.) and (nitride with nucleat\$3)	US-PGPUB; USPAT	OR	ON	2006/02/04 11:06
L1	207	((((438/778) or (438/791) or (438/758) or (438/763) or (438/792) or (438/786)).CCLS.) and (ald)	US-PGPUB; USPAT	OR	ON	2006/02/04 11:06
S328	236	S327 and @ad<="20000821"	US-PGPUB; USPAT	OR	ON	2006/02/03 14:16
S327	520	isolation with bpsg	US-PGPUB; USPAT	OR	ON	2006/02/03 14:16
S326	520	isolation with bpsg	US-PGPUB; USPAT	OR	ON	2006/02/03 14:16
S325	0	((silicon adj (oxide with nitride)) or "sio.sub.2" or "si.sub.3n.sub.4" or "si.sub.xn.sub.y") with cvd with (insitu or "in situ")	US-PGPUB; USPAT	OR	ON	2006/02/03 13:44
S324	0	((silicon adj (oxide with nitride) or "sio.sub.2" or "si.sub.3n.sub.4" or "si.sub.xn.sub.y")) with cvd with (insitu or "in situ")	US-PGPUB; USPAT	OR	ON	2006/02/03 13:44
S323	0	(silicon adj (oxide with nitride)) with cvd with (insitu or "in situ")	US-PGPUB; USPAT	OR	ON	2006/02/03 13:43
S321	45	(ald with cvd) and (ald with (cvd adj chamber))	US-PGPUB; USPAT	OR	ON	2006/02/03 13:41
S322	173	moslehi.inv.	US-PGPUB; USPAT	OR	ON	2006/02/03 13:12
S320	70	S316 and cvd	US-PGPUB; USPAT	OR	ON	2006/02/03 13:05
S319	1	S316 and ale	US-PGPUB; USPAT	OR	ON	2006/02/03 13:00
S318	0	S316 and ald	US-PGPUB; USPAT	OR	ON	2006/02/03 13:00
S317	7243	S316 adn ald	US-PGPUB; USPAT	OR	ON	2006/02/03 13:00
S316	123	maydan.inv.	US-PGPUB; USPAT	OR	ON	2006/02/03 13:00
S315	169	ald with (sequential or pulsed) with cvd	US-PGPUB; USPAT	OR	ON	2006/02/03 12:58
S313	306	ald with cvd with chamber	US-PGPUB; USPAT	OR	ON	2006/02/03 12:57
S314	0	S313 and multiprocess with chamber	US-PGPUB; USPAT	OR	ON	2006/02/03 12:56
S312	14	((tantalum and aluminum) adj oxide) with (ald and cvd)	US-PGPUB; USPAT	OR	ON	2006/02/03 12:08

S31 1	37	((tantalum and aluminum) adj oxide) with (ald)	US-PGPUB; USPAT	OR	ON	2006/02/03 12:08
S31 0	235	((tantalum or aluminum) adj oxide) with (ald)	US-PGPUB; USPAT	OR	ON	2006/02/03 12:07
S30 9	1377	((tantalum or aluminum) adj oxide) with (ald or cvd)	US-PGPUB; USPAT	OR	ON	2006/02/03 12:06
S30 7	268	(etch\$4 adj stop\$4) with ((tantalum or aluminum) adj oxide)	US-PGPUB; USPAT	OR	ON	2006/02/03 12:06
S30 8	60	(etch\$4 adj stop\$4) with ((tantalum) adj oxide)	US-PGPUB; USPAT	OR	ON	2006/02/03 12:02
S30 6	6	(ald with cvd with ("ex situ" or exsitu))	US-PGPUB; USPAT	OR	ON	2006/02/03 11:57
S30 5	2	(ald with cvd with ("in situ" or insitu))	US-PGPUB; USPAT	OR	ON	2006/02/03 11:56
S30 3	354	(ald with cvd with (chamber or reactor or station))	US-PGPUB; USPAT	OR	ON	2006/02/03 11:56
S30 4	50	("5480818").URPN.	USPAT	OR	ON	2006/02/03 11:50
S30 2	1	(ald with cvd with (chamber or reactor or station)) with (insitu or "in situ")	US-PGPUB; USPAT	OR	ON	2006/02/03 11:44
S30 0	217	S299 and ald	US-PGPUB; USPAT	OR	ON	2006/02/03 10:46
S30 1	0	S300 and (((silicon adj (nitride oxide dioxide)) and "sio.sub.2" or "si.sub.3n.sub.4" "si.sub.xn.sub.y") with (insitu or "in situ"))	US-PGPUB; USPAT	OR	ON	2006/02/03 10:45
S29 9	27168	samsung.as.	US-PGPUB; USPAT	OR	ON	2006/02/03 10:45
S29 8	1	smsung.as.	US-PGPUB; USPAT	OR	ON	2006/02/03 10:45
S29 5	378	((silicon adj (nitride oxide dioxide)) or "sio.sub.2" or "si.sub.3n.sub.4" "si.sub.xn.sub.y") with (insitu or "in situ")	US-PGPUB; USPAT	OR	ON	2006/02/03 10:45
S29 7	4	S290 and S295	US-PGPUB; USPAT	OR	ON	2006/02/03 10:44
S29 6	0	S295 and (cvd with ald with (insitu or "in situ"))	US-PGPUB; USPAT	OR	ON	2006/02/03 10:44
S29 1	1005	S290 and ((silicon adj (nitride oxide dioxide)) or "sio.sub.2" or "si.sub.3n.sub.4" "si.sub.xn.sub.y")	US-PGPUB; USPAT	OR	ON	2006/02/03 10:42
S29 4	2	S291 and (ald with (insitu or "in situ"))	US-PGPUB; USPAT	OR	ON	2006/02/03 10:40
S29 3	78	S291 and (insitu or "in situ")	US-PGPUB; USPAT	OR	ON	2006/02/03 10:40
S29 2	13	S291 and @ad<="20000822"	US-PGPUB; USPAT	OR	ON	2006/02/03 10:11

S29 0	1114	(dielectric ild "interlayer dielectric" "interlevel dielectric" "interlayer insulating" "interlevel insulating") with ald	US-PGPUB; USPAT	OR	ON	2006/02/03 10:10
S28 9	4	S288 and ald	US-PGPUB; USPAT	OR	ON	2006/02/03 10:09
S28 8	223	((438/907) or (438/908)).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/02/03 09:56
S28 7	21	S286 and ("insitu" or "in situ") and ("exsitu" or "ex situ")	US-PGPUB; USPAT	OR	ON	2006/02/03 09:56
S28 6	1227	(insulating dielectric) with ald	US-PGPUB; USPAT	OR	ON	2006/02/03 09:47
S28 5	1085	dielectric with ald	US-PGPUB; USPAT	OR	ON	2006/02/03 09:46
S28 1	30	(ild or "interlayer dielectric") with (ald)	US-PGPUB; USPAT	OR	ON	2006/02/03 09:46
S28 4	11	("5366953").URPN.	USPAT	OR	ON	2006/02/03 09:10
S28 3	51	(ild or "interlayer dielectric" or "interlayer insulating") with (ald)	US-PGPUB; USPAT	OR	ON	2006/02/03 09:07
S28 2	1	("5597756").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/02/03 09:06